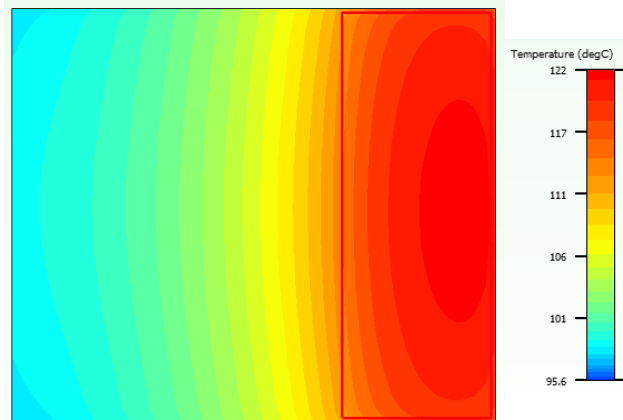


TAS5825 Results

- Power dissipation concentrated in power FET shown to right
- 50 mW additional power dissipation on remainder of die
- 2 different conditions were modeled
 - Condition1: 25 °C Ambient, 4 W on Power FET (2×25W into 8ohm@PVDD=24V)
 - Condition2: 25 °C Ambient, 2 W on Power FET
- These models reflect various specific test cases and use conditions and do not guarantee that the device will function in a customer system.

	Condition 1	Condition 2
Max Die Temp	122.0 °C	74.9 °C
Ambient	25.9 °C	25.5 °C
Max Case Temp	118.1 °C	73.0 °C
Center Case Temp	105.9 °C	67.5 °C
Eff. Theta-JA	23.7 °C/W	24.1 °C/W



Example Die Temperature Map from Case 1